

ABSTRACT OF THE DISCLOSURE

Provided is a quartz glass crucible capable of achieving both improvement of manufacturing yield of silicon single crystals and suppression of generation of
5 pinholes in single crystals.

A quartz glass crucible 1 includes: a straight body portion 1a having a cylindrical shape; a bottom portion 1b which is curved; and a corner portion 1c provided between the straight body portion 1a and the bottom portion 1b, in
10 which a bubble content of an inner surface layer portion ranging from an inner surface to a depth 0.5 mm in an upper portion 1a₁ of the straight body portion 1a is 0.2% or more and 2% or less, the bubble content of the inner surface layer portion in a lower portion 1a₂ of the
15 straight body portion 1a is more than 0.1% and not more than 1.3 times a lower limit of the bubble content of the upper portion 1a₁ of the straight body portion 1a, the bubble content of the inner surface layer portion in the corner portion 1c is more than 0.1% and 0.5% or less, and
20 the bubble content of the inner surface layer portion in the bottom portion 1b is 0.1% or less.